

600V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

TO-220F GDS	TO-220 GDS
	G

Device Marking and Package Information			
Device Package Marking			
CS10N60F	TO-220F	CS10N60F	
CS10N60P	TO-220	CS10N60P	

Absolute Maximum Ratings $T_c = 25^{\circ}C$, unless otherwise noted					
Parameter	Symbol	Value		Unit	
Falalletei	Symbol	TO-220F	TO-220		
Drain-Source Voltage ($V_{GS} = 0V$)	V _{DSS}	60	00	V	
Continuous Drain Current	I _D	10		A	
Pulsed Drain Current (note1)	I _{DM}	40		A	
Gate-Source Voltage	V _{GSS}	±	30	V	
Single Pulse Avalanche Energy (note2)	E _{AS}	320		mJ	
Avalanche Current (note1)	I _{AS}	8		А	
Repetitive Avalanche Energy (note1)	E _{AR}	190		mJ	
Power Dissipation ($T_c = 25^{\circ}C$)	P _D	32	65	W	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~-	+150	°C	

Thermal Resistance				
Parameter	Symbol	Va	L I wit	
	Symbol	TO-220F	TO-220	Unit
Thermal Resistance, Junction-to-Case	R _{thJC}	1.92	0.89	
Thermal Resistance, Junction-to-Ambient	R _{thJA}	62.5	60	K/W



CS10N60F,CS10N60P

Specifications $T_J = 25^{\circ}C$, unless otherwise noted							
Parameter	Cumple of	bol Test Conditions	Value			Unit	
raiametei	Symbol		Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_{D} = 250 \mu A$	600			V	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 600V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	μA	
Gate-Source Leakage	I _{GSS}	V_{GS} = $\pm 30V$			±100	nA	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	3.0		4.0	V	
Drain-Source On-Resistance (Note3)	R _{DS(on)}	V _{GS} = 10V, I _D = 5.0A		0.6	0.72	Ω	
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0V,		1363		pF	
Output Capacitance	C _{oss}	$V_{DS} = 25V,$		139			
Reverse Transfer Capacitance	C _{rss}	f = 1.0MHz		18			
Total Gate Charge	Q_{g}			42			
Gate-Source Charge	Q_{gs}	$V_{DD} = 480V, I_D = 10A, V_{GS} = 10V$		6		nC	
Gate-Drain Charge	Q_{gd}			22			
Turn-on Delay Time	t _{d(on)}			45			
Turn-on Rise Time	t _r	V _{DD} = 300V, I _D =10A,		28		20	
Turn-off Delay Time	t _{d(off)}	$R_{\rm G} = 25 \ \Omega$		190		ns	
Turn-off Fall Time	t _f			75			
Drain-Source Body Diode Character	istics						
Continuous Body Diode Current	I _s	T - 25.9C			10	۸	
Pulsed Diode Forward Current	I _{SM}	T _C = 25 °C			40	A	
Body Diode Voltage	V_{SD}	$T_J = 25^{\circ}C, I_{SD} = 5A, V_{GS} = 0V$			1.4	V	
Reverse Recovery Time	t _{rr}	$V_{GS} = 0V, I_S = 10A,$ $di_F/dt = 100A /\mu s$		552		ns	
Reverse Recovery Charge	Q _{rr}			2.76		μC	

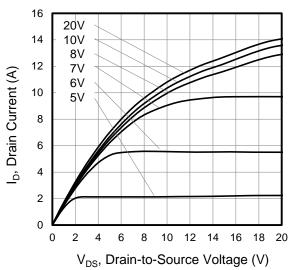
Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L=10mH, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25 °C
- 3. Pulse Test: Pulse width \leq 300µs, Duty Cycle \leq 1%

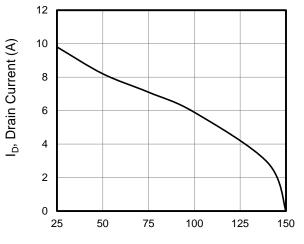


Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

Figure 1. Output Characteristics (T_J = 25°C)

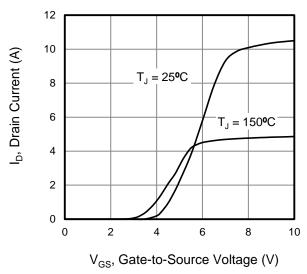






T_C, Case Temperature (A)





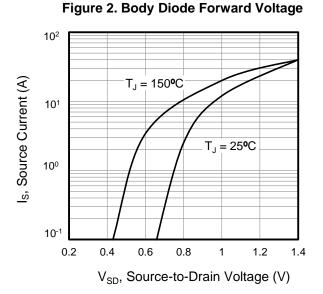


Figure 4. BV_{DSS} Variation vs. Temperature

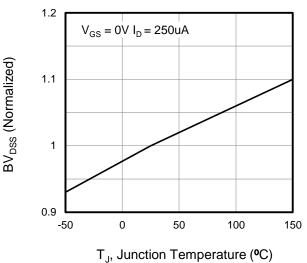
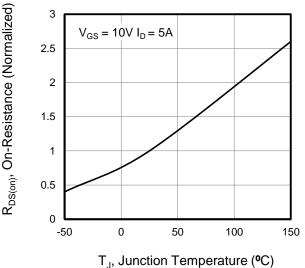


Figure 6. On-Resistance vs. Temperature





Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

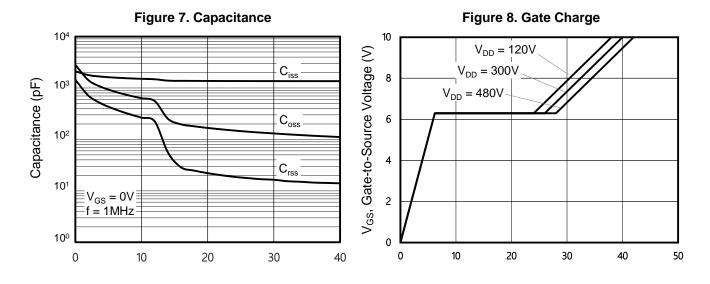
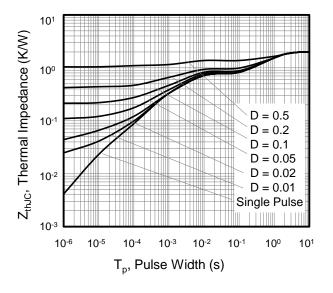


Figure 9. Transient Thermal Impedance







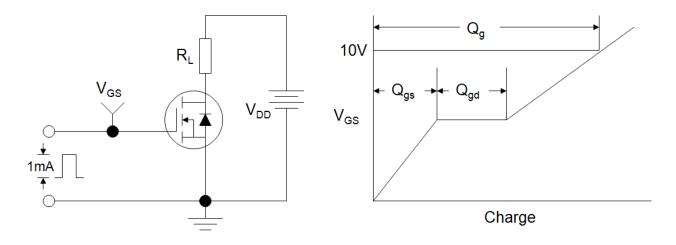


Figure B: Resistive Switching Test Circuit and Waveform

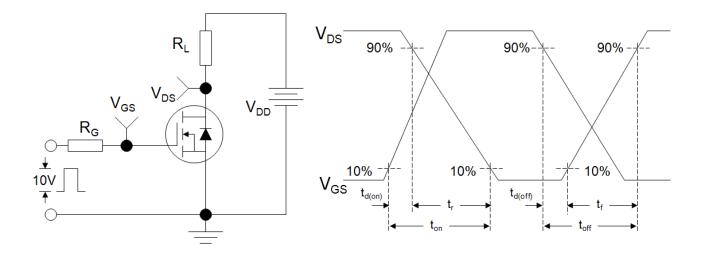
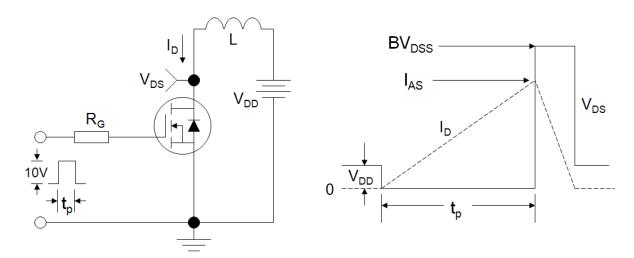


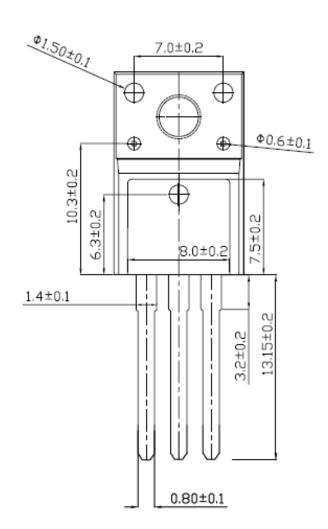
Figure C: Unclamped Inductive Switching Test Circuit and Waveform

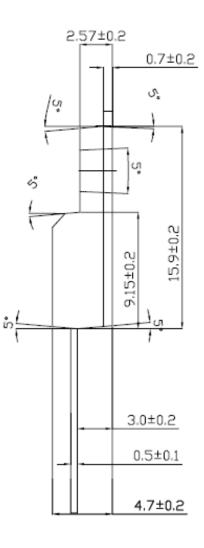






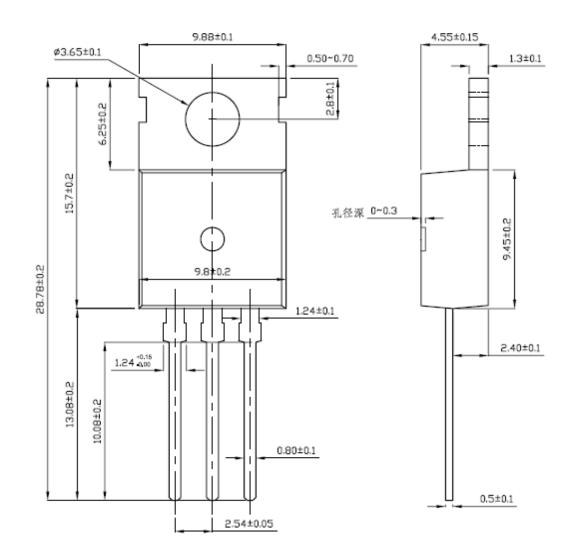
TO-220F







TO-220





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